

Preliminary Amendment

Applicant: Michael Kund et al.

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Title: MEMORY CELL AND METHOD FOR FABRICATING A MEMORY DEVICE (As Amended)

IN THE ABSTRACT

Please replace the Abstract with the following rewritten paragraph:

Abstract

MEMORY CELL AND METHOD FOR FABRICATING A MEMORY
DEVICE~~**MEMORY CELL AND METHOD FOR FABRICATING A MEMORY**~~
DEVICE

Abstract

When fabricating a memory cell (1) with an organic storage layer (10) which stores a digital information item, processing of polycrystalline and monocrystalline semiconductor structures in which high temperatures are employed is concluded prior to application of the organic storage layer (10).

(Fig. 2)